



# RF Power Field Effect Transistor

## N-Channel Enhancement-Mode Lateral MOSFET

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

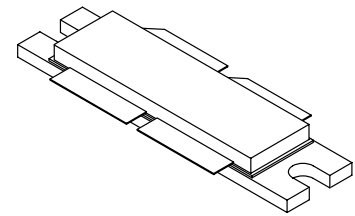
- Typical 2-Carrier W-CDMA Performance:  $V_{DD} = 28$  Volts,  $I_{DQ} = 2200$  mA,  $P_{out} = 52$  Watts Avg., Full Frequency Band, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.  
Power Gain — 13 dB  
Drain Efficiency — 24%  
IM3 @ 10 MHz Offset — -36 dBc in 3.84 MHz Channel Bandwidth  
ACPR @ 5 MHz Offset — -39 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 5:1 VSWR, @ 28 Vdc, 2140 MHz, 180 Watts CW Output Power

### Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32  $V_{DD}$  Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Low Gold Plating Thickness on Leads, 40 $\mu$ m Nominal.
- RoHS Compliant
- In Tape and Reel. R6 Suffix = 150 Units per 56 mm, 13 inch Reel.

**MRF5P21240HR6**

**2110-2170 MHz, 52 W AVG., 28 V  
2 x W-CDMA  
LATERAL N-CHANNEL  
RF POWER MOSFET**



**CASE 375D-05, STYLE 1  
NI-1230**

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +65	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25 $^\circ\text{C}$	$P_D$	603 3.4	W W/ $^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Case Operating Temperature	$T_C$	150	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	200	$^\circ\text{C}$
CW Operation @ $T_C = 25^\circ\text{C}$ Derate above 25 $^\circ\text{C}$	CW	200 1.18	W W/ $^\circ\text{C}$

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 82 $^\circ\text{C}$ , 180 W CW Case Temperature 77 $^\circ\text{C}$ , 52 W CW	$R_{\theta JC}$	0.29 0.32	$^\circ\text{C}/\text{W}$

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

**Table 3. ESD Protection Characteristics**

Test Conditions	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	M3 (Minimum)
Charge Device Model (per JESD22-C101)	C6 (Minimum)

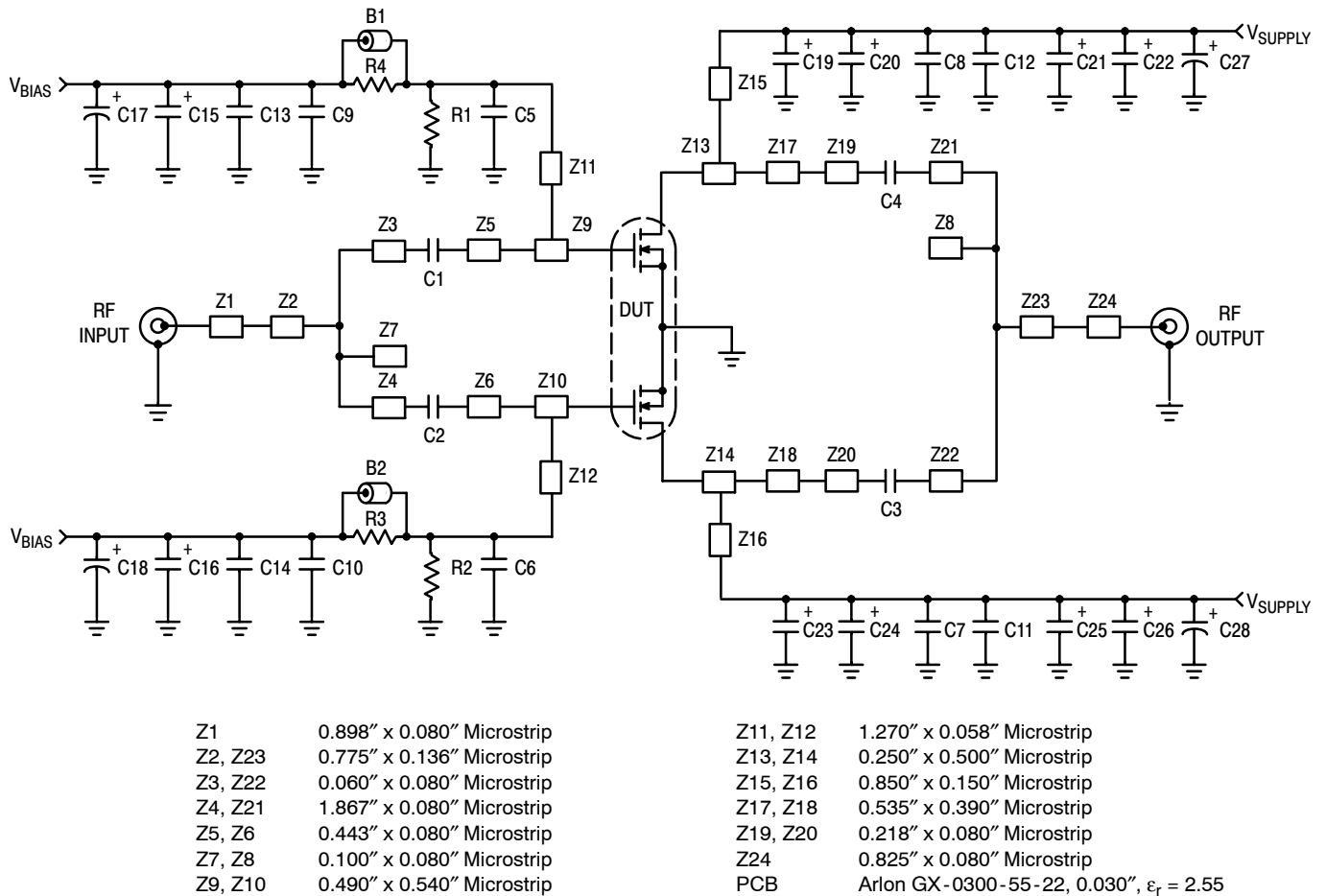
**Table 4. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Off Characteristics</b> <sup>(1)</sup>					
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 65\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	1	$\mu\text{Adc}$
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	1	$\mu\text{Adc}$
<b>On Characteristics</b>					
Gate Threshold Voltage <sup>(1)</sup> ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 300\ \mu\text{Adc}$ )	$V_{GS(th)}$	2	2.8	4	Vdc
Gate Quiescent Voltage <sup>(3)</sup> ( $V_{DS} = 28\text{ Vdc}$ , $I_D = 2200\text{ mAdc}$ )	$V_{GS(Q)}$	3	3.8	5	Vdc
Drain-Source On-Voltage <sup>(1)</sup> ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 3\text{ Adc}$ )	$V_{DS(on)}$	—	0.26	0.3	Vdc
Forward Transconductance <sup>(1)</sup> ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 3\text{ Adc}$ )	$g_{fs}$	—	7.5	—	S
<b>Dynamic Characteristics</b> <sup>(1,2)</sup>					
Reverse Transfer Capacitance ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0$ , $f = 1\text{ MHz}$ )	$C_{rss}$	—	2.75	—	pF

**Functional Tests** <sup>(3)</sup> (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 2200\text{ mA}$ ,  $P_{out} = 52\text{ W Avg.}$ ,  $f_1 = 2112.5\text{ MHz}$ ,  $f_2 = 2122.5\text{ MHz}$  and  $f_1 = 2157.5\text{ MHz}$ ,  $f_2 = 2167.5\text{ MHz}$ , 2-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @  $\pm 5\text{ MHz}$  Offset. IM3 measured in 3.84 MHz Bandwidth @  $\pm 10\text{ MHz}$  Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.

Power Gain	$G_{ps}$	12	13	—	dB
Drain Efficiency	$\eta_D$	22.5	24	—	%
Intermodulation Distortion	IM3	—	-36	-34	dBc
Adjacent Channel Power Ratio	ACPR	—	-39	-37	dBc
Input Return Loss	IRL	—	-12	-9	dB

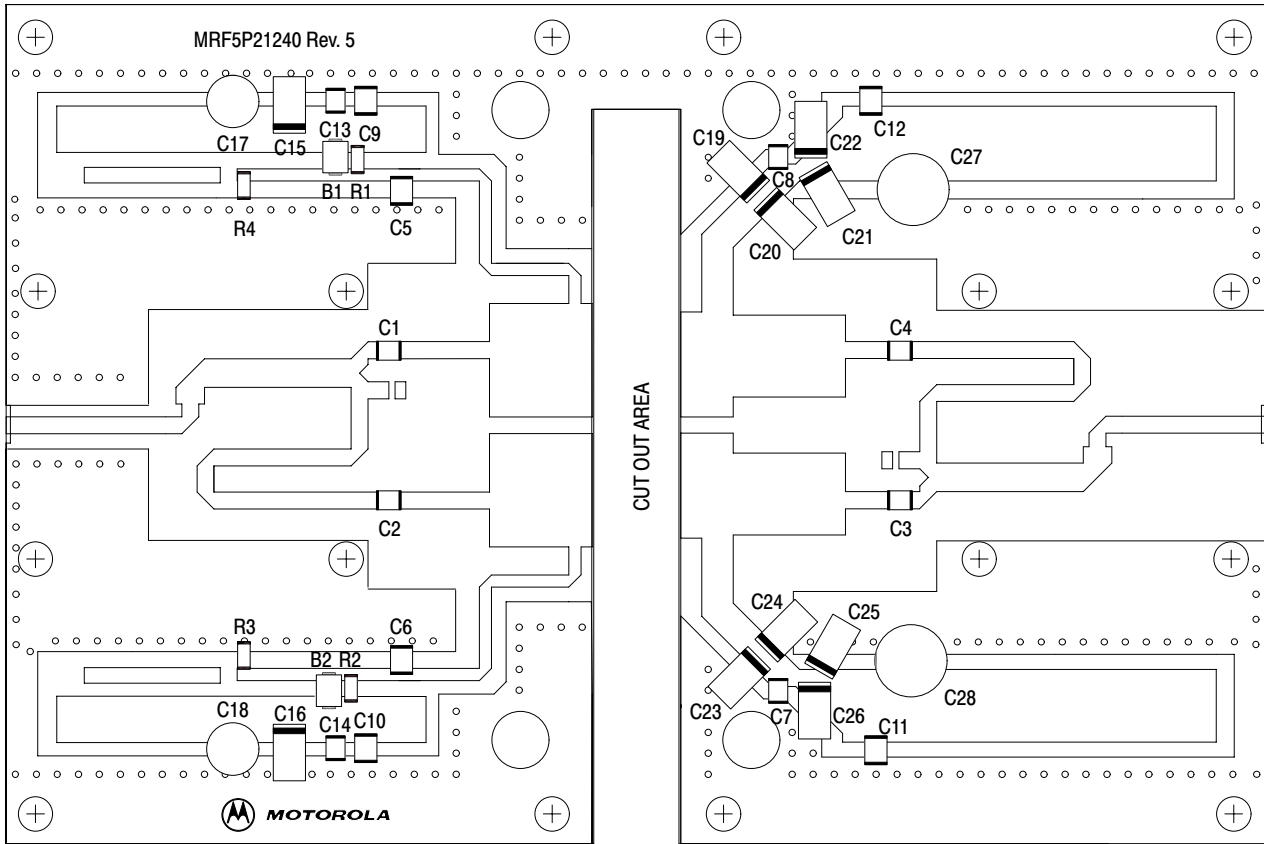
1. Each side of device measured separately.
2. Part internally matched both on input and output.
3. Measurement made with device in push-pull configuration.



**Figure 1. MRF5P21240HR6 Test Circuit Schematic**

**Table 5. MRF5P21240HR6 Test Circuit Component Designations and Values**

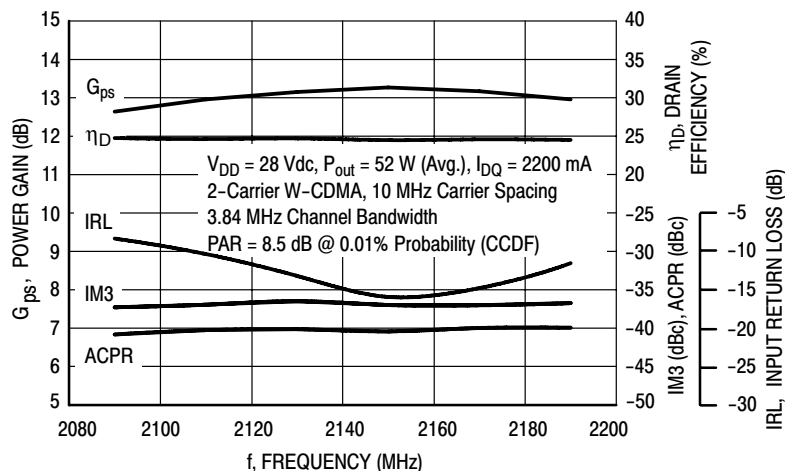
Part	Description	Part Number	Manufacturer
B1, B2	Short Ferrite Beads	2743019447	Fair Rite
C1, C2, C3, C4	18 pF Chip Capacitors	100B180JCA500X	ATC
C5, C6, C7, C8	6.8 pF Chip Capacitors	100B6R8JCA500X	ATC
C9, C10, C11, C12	0.1 $\mu$ F Chip Capacitors	CDR33BX104AKWS	Kemet
C13, C14	1000 pF Chip Capacitors	100B102JCA500X	ATC
C15, C16	4.7 $\mu$ F Tantalum Capacitors	T491C475M050	Kemet
C17, C18	10 $\mu$ F Electrolytic Capacitors	EEV-HB1H100P	Panasonic
C19, C20, C21, C22 C23, C24, C25, C26	22 $\mu$ F Tantalum Capacitors	T491X226K035AS4394	Kemet
C27, C28	100 $\mu$ F Electrolytic Capacitors	517D107M050BB6A	Sprague
R1, R2	1.0 k $\Omega$ , 1/8 W Chip Resistors		
R3, R4	10 $\Omega$ , 1/8 W Chip Resistors		



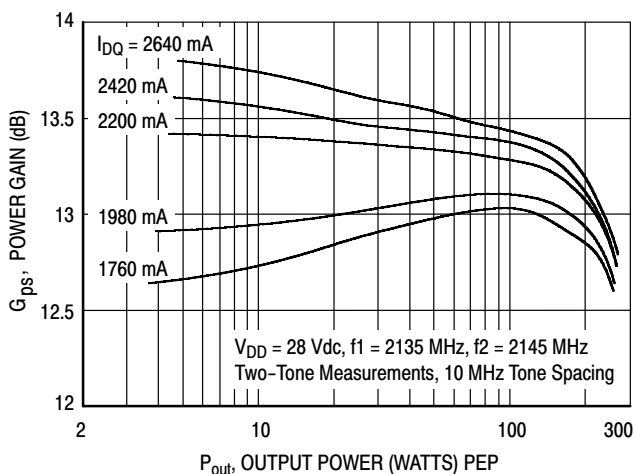
Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

**Figure 2. MRF5P21240HR6 Test Circuit Component Layout**

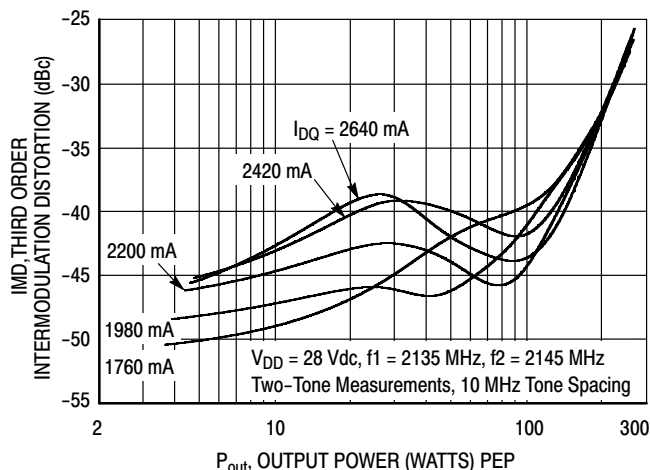
## TYPICAL CHARACTERISTICS



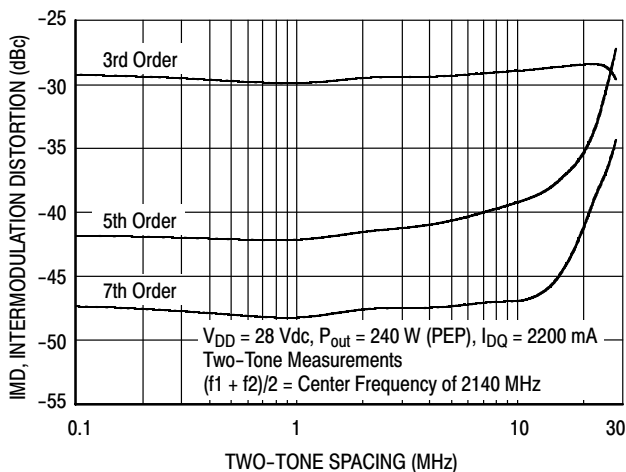
**Figure 3. 2-Carrier W-CDMA Broadband Performance  
@  $P_{out} = 52$  Watts Avg.**



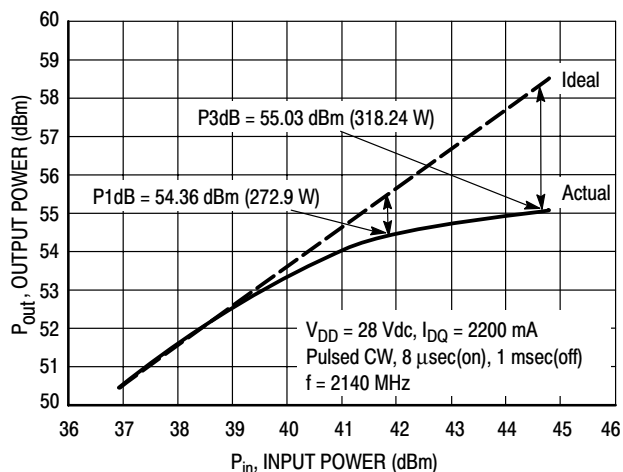
**Figure 4. Two-Tone Power Gain versus  
Output Power**



**Figure 5. Third Order Intermodulation Distortion  
versus Output Power**

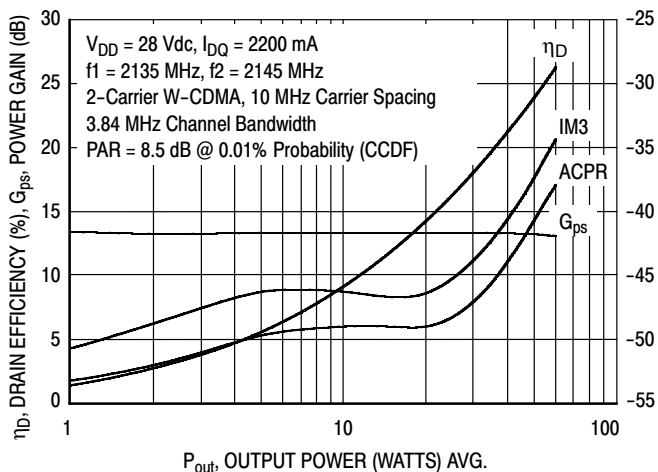


**Figure 6. Intermodulation Distortion Products  
versus Tone Spacing**

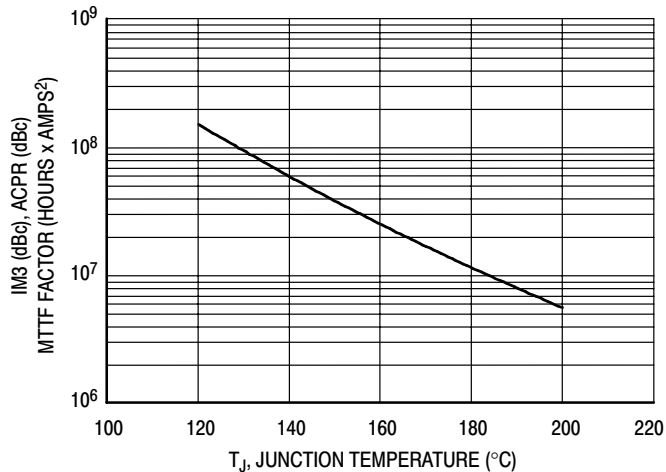


**Figure 7. Pulse CW Output Power versus  
Input Power**

## TYPICAL CHARACTERISTICS



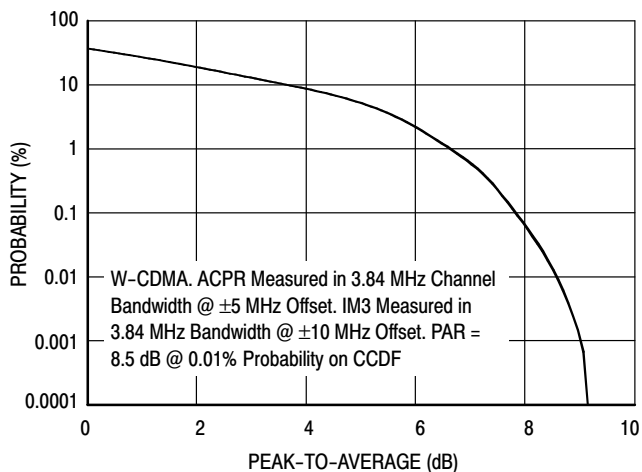
**Figure 8. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power**



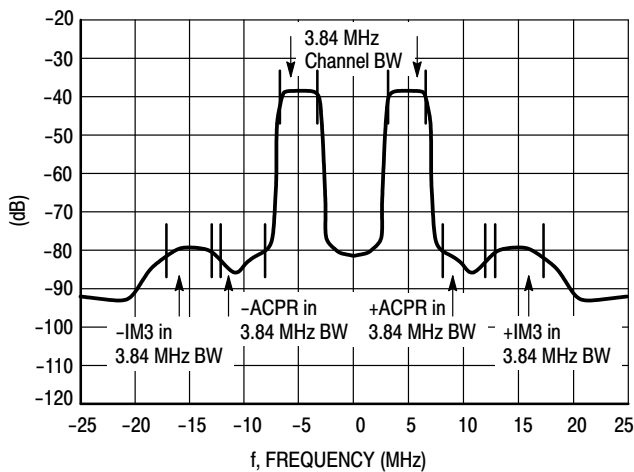
This above graph displays calculated MTTF in hours x ampere<sup>2</sup> drain current. Life tests at elevated temperatures have correlated to better than  $\pm 10\%$  of the theoretical prediction for metal failure. Divide MTTF factor by  $I_D^2$  for MTTF in a particular application.

**Figure 9. MTTF Factor versus Junction Temperature**

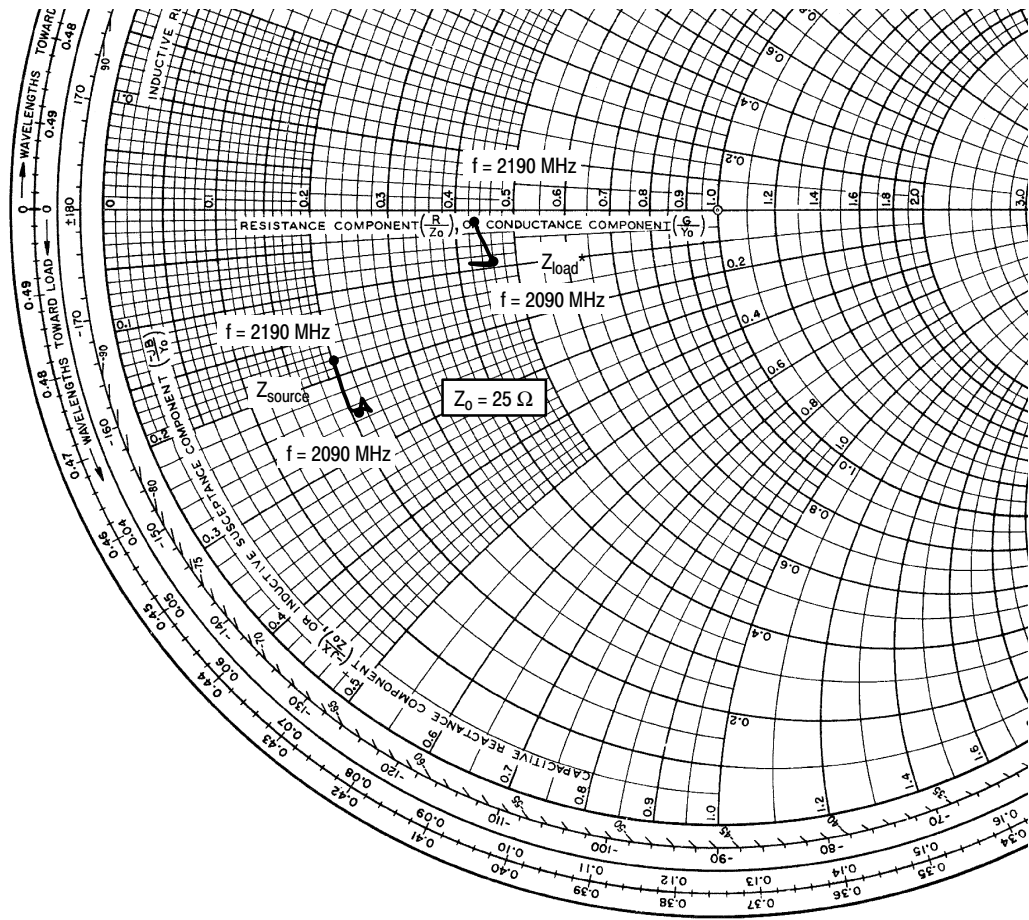
## W-CDMA TEST SIGNAL



**Figure 10. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal**



**Figure 11. 2-Carrier W-CDMA Spectrum**



$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 2200 \text{ mA}$ ,  $P_{out} = 52 \text{ W Avg.}$

f MHz	$Z_{source}$ Ω	$Z_{load}$ Ω
2090	5.33 - j6.21	11.42 - j2.25
2110	5.44 - j5.88	10.45 - j2.16
2130	5.40 - j6.16	11.28 - j2.14
2150	5.12 - j6.06	11.38 - j2.14
2170	4.96 - j5.25	11.04 - j1.25
2190	4.98 - j4.47	10.73 - j0.40

$Z_{source}$  = Test circuit impedance as measured from gate to gate, balanced configuration.

$Z_{load}$  = Test circuit impedance as measured from drain to drain, balanced configuration.

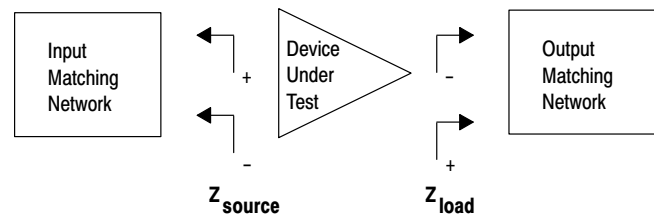


Figure 12. Series Equivalent Source and Load Impedance

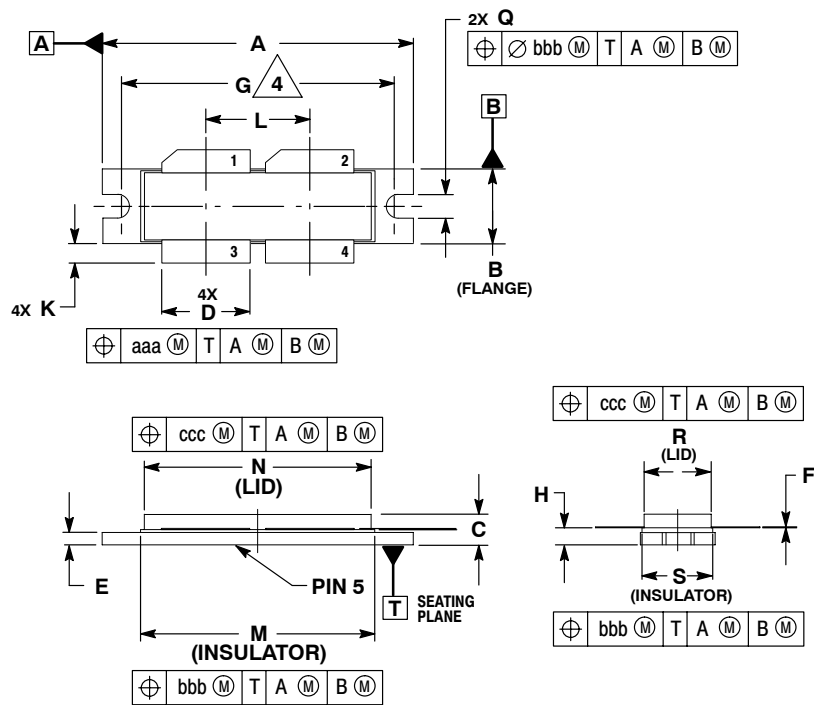
# NOTES



# NOTES

# NOTES

## PACKAGE DIMENSIONS



**NOTES:**

1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
4. △ RECOMMENDED BOLT CENTER DIMENSION OF 1.52 (38.61) BASED ON M3 SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.28
B	0.395	0.405	10.03	10.29
C	0.150	0.200	3.81	5.08
D	0.455	0.465	11.56	11.81
E	0.062	0.066	1.57	1.68
F	0.004	0.007	0.10	0.18
G	1.400 BSC		35.56 BSC	
H	0.082	0.090	2.08	2.29
K	0.117	0.137	2.97	3.48
L	0.540 BSC		13.72 BSC	
M	1.219	1.241	30.96	31.52
N	1.218	1.242	30.94	31.55
Q	0.120	0.130	3.05	3.30
R	0.355	0.365	9.01	9.27
S	0.365	0.375	9.27	9.53
aaa	0.013 REF		0.33 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.020 REF		0.51 REF	

**STYLE 1:**

- PIN 1. DRAIN
2. DRAIN
3. GATE
4. GATE
5. SOURCE

**CASE 375D-05  
ISSUE E  
NI-1230**

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